

C4D50120H

Silicon Carbide Schottky Diode

V_{RRM}	=	1200	V
$I_F (T_C \leq 135^\circ\text{C})$	=	62	A
Q_C	=	143	nC

Features

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on V_F
- Temperature-independent Switching
- 175°C Operating Junction Temperature

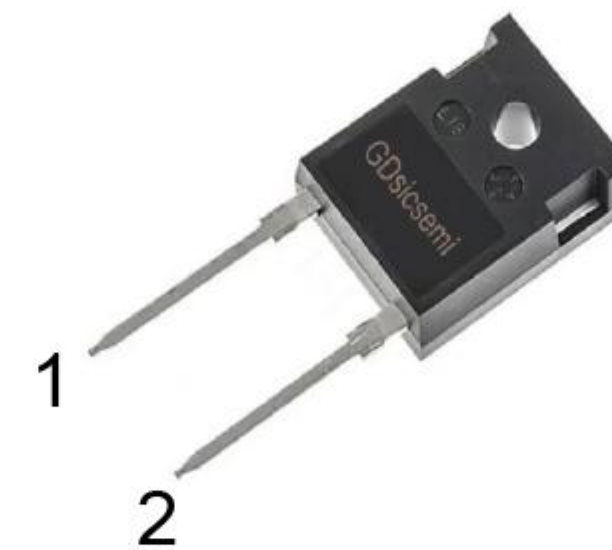
Benefits

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Package



TO-247-2



Part Number	Package	Marking
C4D50120H	TO-247-2	C4D50120H

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V	$T_C = 25^\circ\text{C}$	
V_{RSM}	Surge Peak Reverse Voltage	1200	V	$T_C = 25^\circ\text{C}$	
V_R	DC Blocking Voltage	1200	V	$T_C = 25^\circ\text{C}$	
I_F	Forward Current	62 50	A	$T_C \leq 135^\circ\text{C}$ $T_C \leq 147^\circ\text{C}$	
I_{FSM}	Non-Repetitive Forward Surge Current	350	A	$T_C = 25^\circ\text{C}$, $t_p = 8.3\text{ms}$, Half Sine Wave	
P_{tot}	Power Dissipation	600	W	$T_C = 25^\circ\text{C}$	Fig.3
T_C	Maximum Case Temperature	147	$^\circ\text{C}$		
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to 175	$^\circ\text{C}$		
	TO-247 Mounting Torque	1	Nm	M3 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.6 2.25	1.8 2.7	V	$I_F = 50A, T_J = 25^\circ C$ $I_F = 50A, T_J = 175^\circ C$	Fig.1
I_R	Reverse Current	30 100	150 1000	μA	$V_R = 1200V, T_J = 25^\circ C$ $V_R = 1200V, T_J = 175^\circ C$	Fig.2
C	Total Capacitance	3100 220 180	/	pF	$V_R = 0V, T_J = 25^\circ C, f = 1MHz$ $V_R = 400V, T_J = 25^\circ C, f = 1MHz$ $V_R = 800V, T_J = 25^\circ C, f = 1MHz$	Fig.5
Q_C	Total Capacitive Charge	143	/	nC	$V_R = 800V, I_F = 50A$ $di/dt = 200A/\mu s, T_J = 25^\circ C$	Fig.4

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.25	$^\circ C/W$	Fig.6
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	80	$^\circ C/W$	
T_{sold}	Soldering Temperature	260	$^\circ C$	

Typical Performance

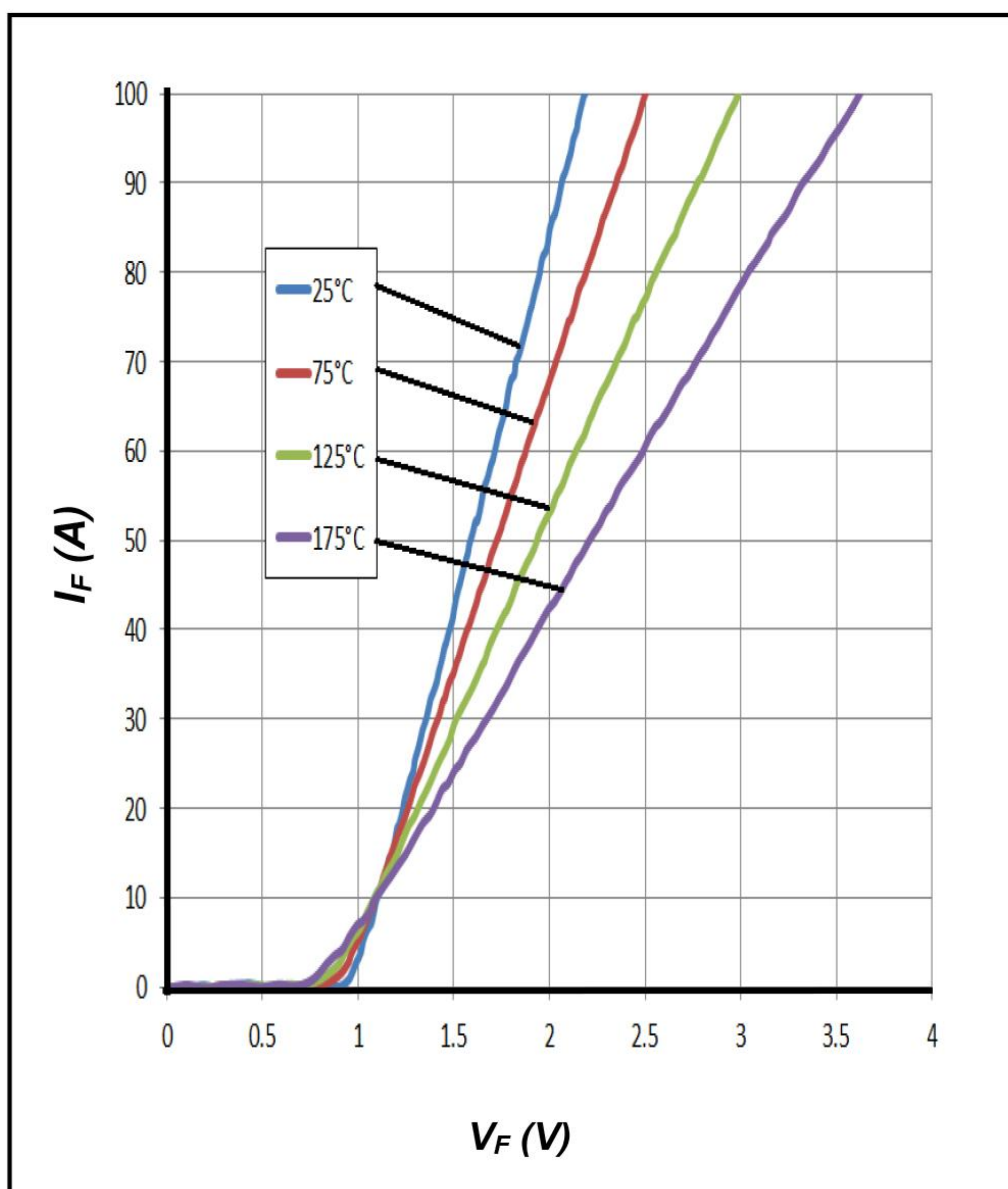


Figure 1. Forward Characteristics

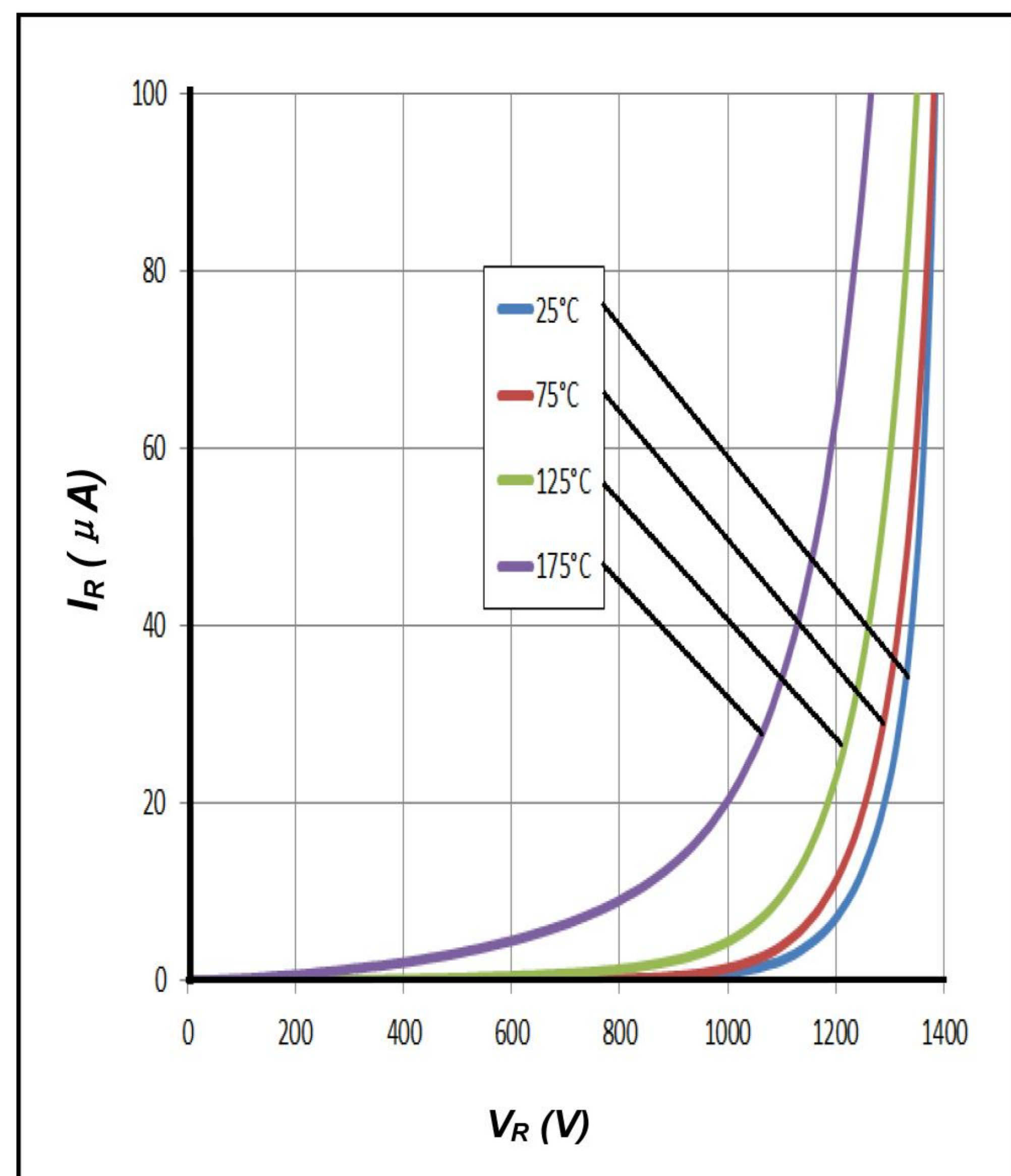


Figure 2. Reverse Characteristics

Typical Performance

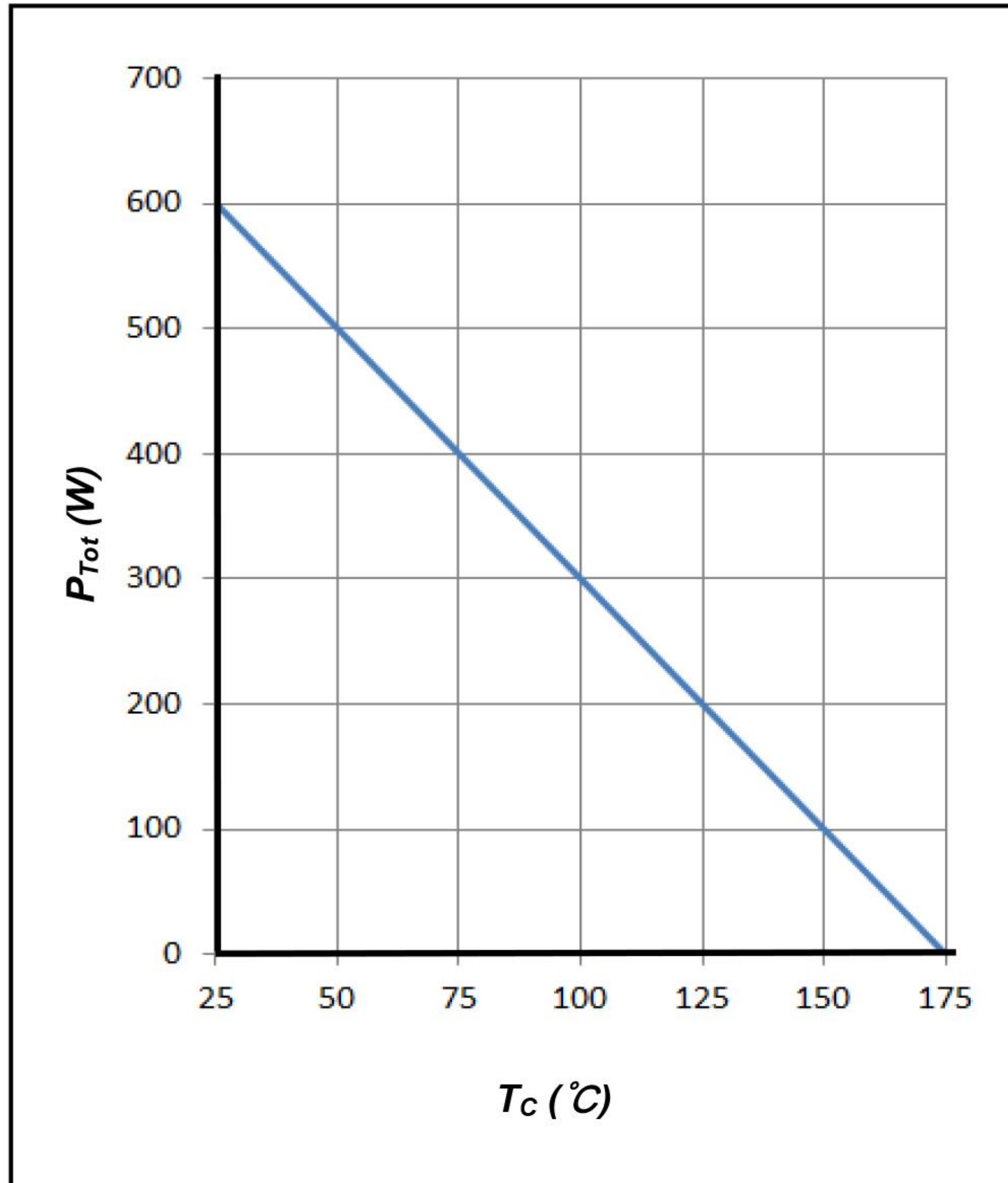


Figure 3. Power Derating

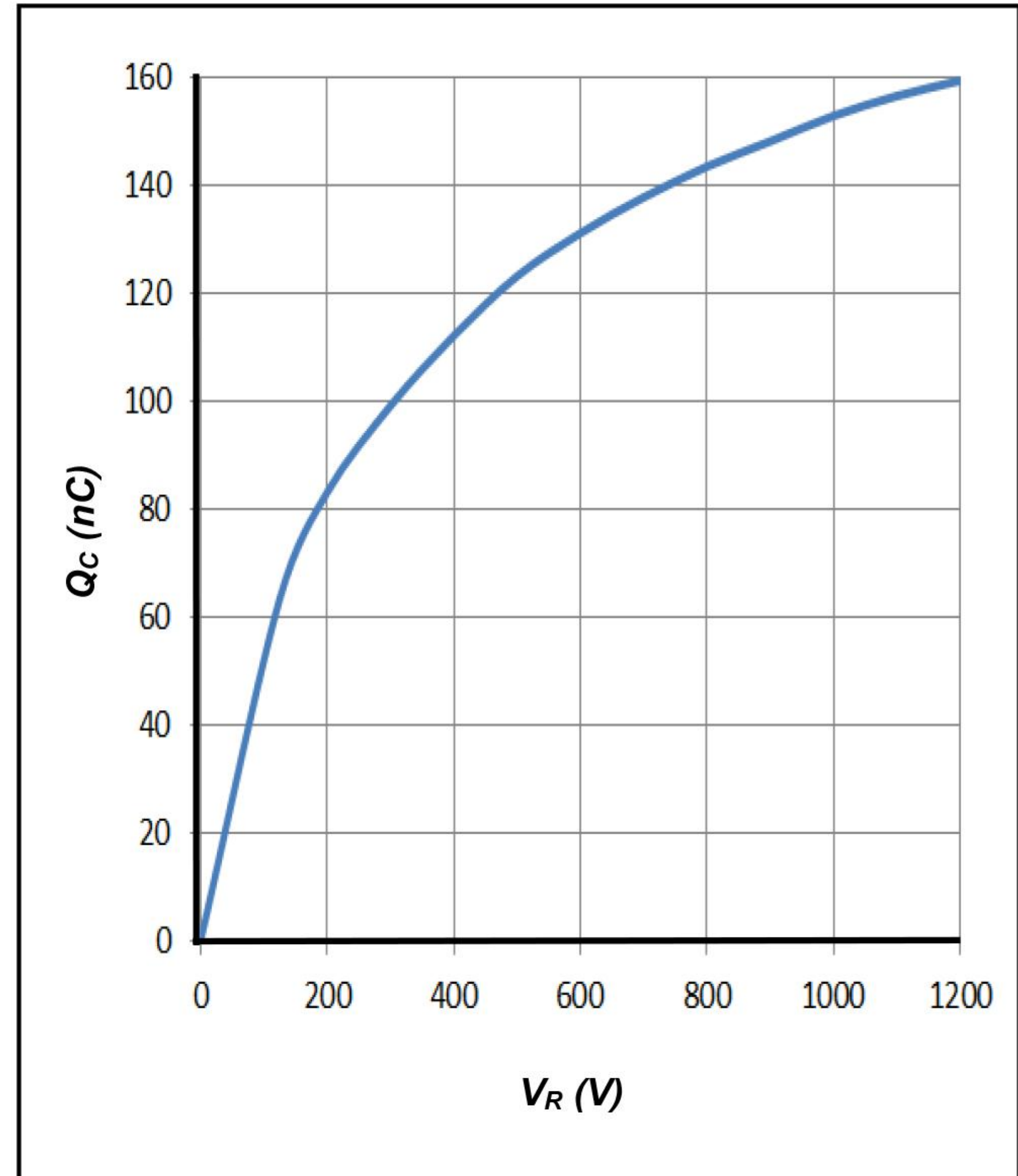


Figure 4. Total Capacitive Charge vs. Reverse Voltage



Figure 5. Total Capacitance vs. Reverse Voltage

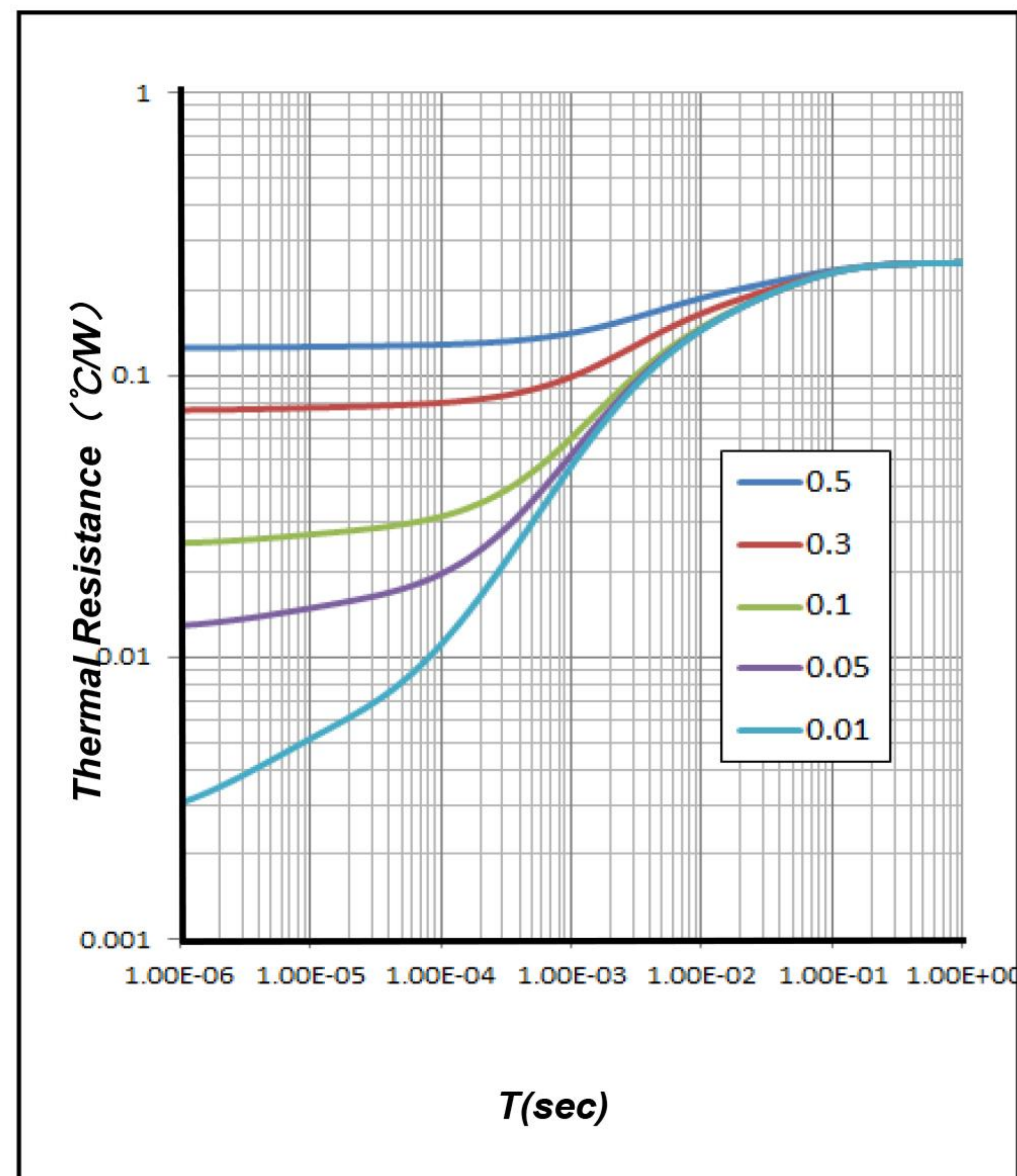
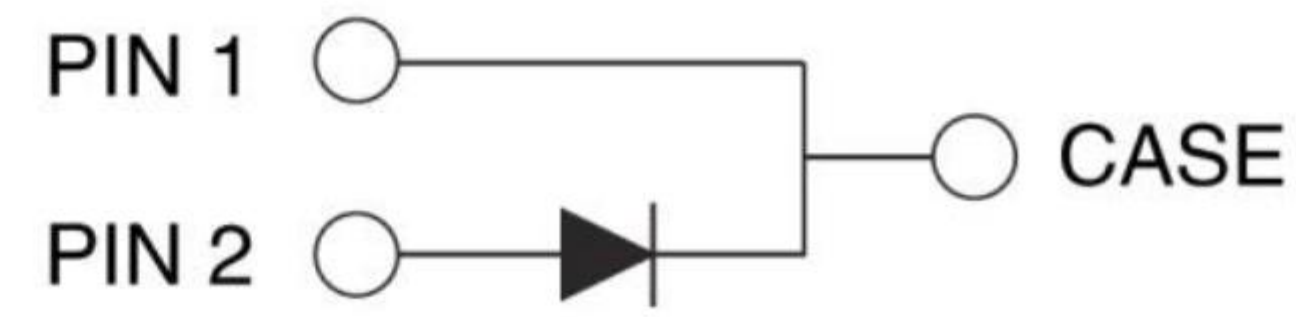
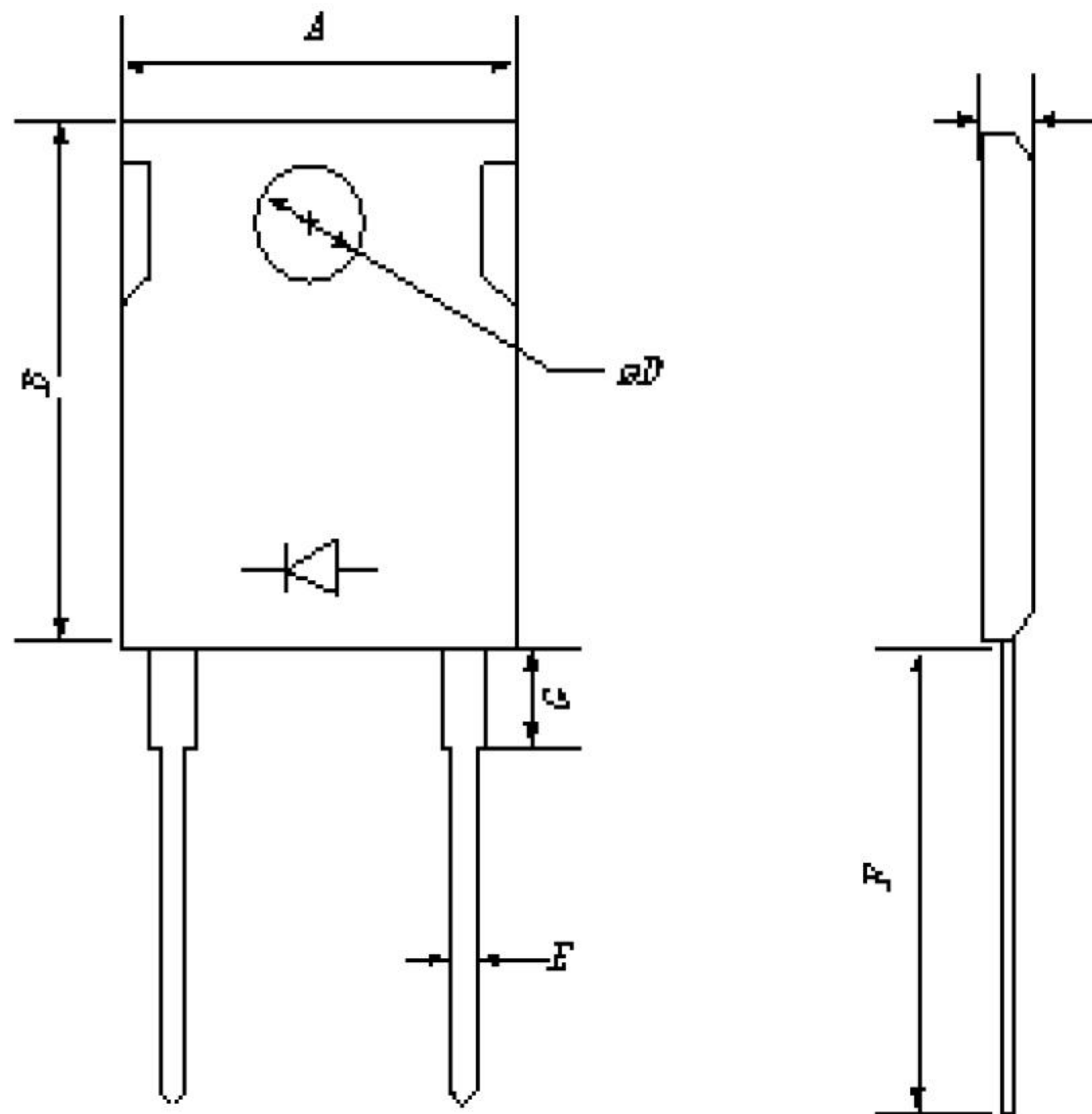


Figure 6. Transient Thermal Impedance

Package Dimensions

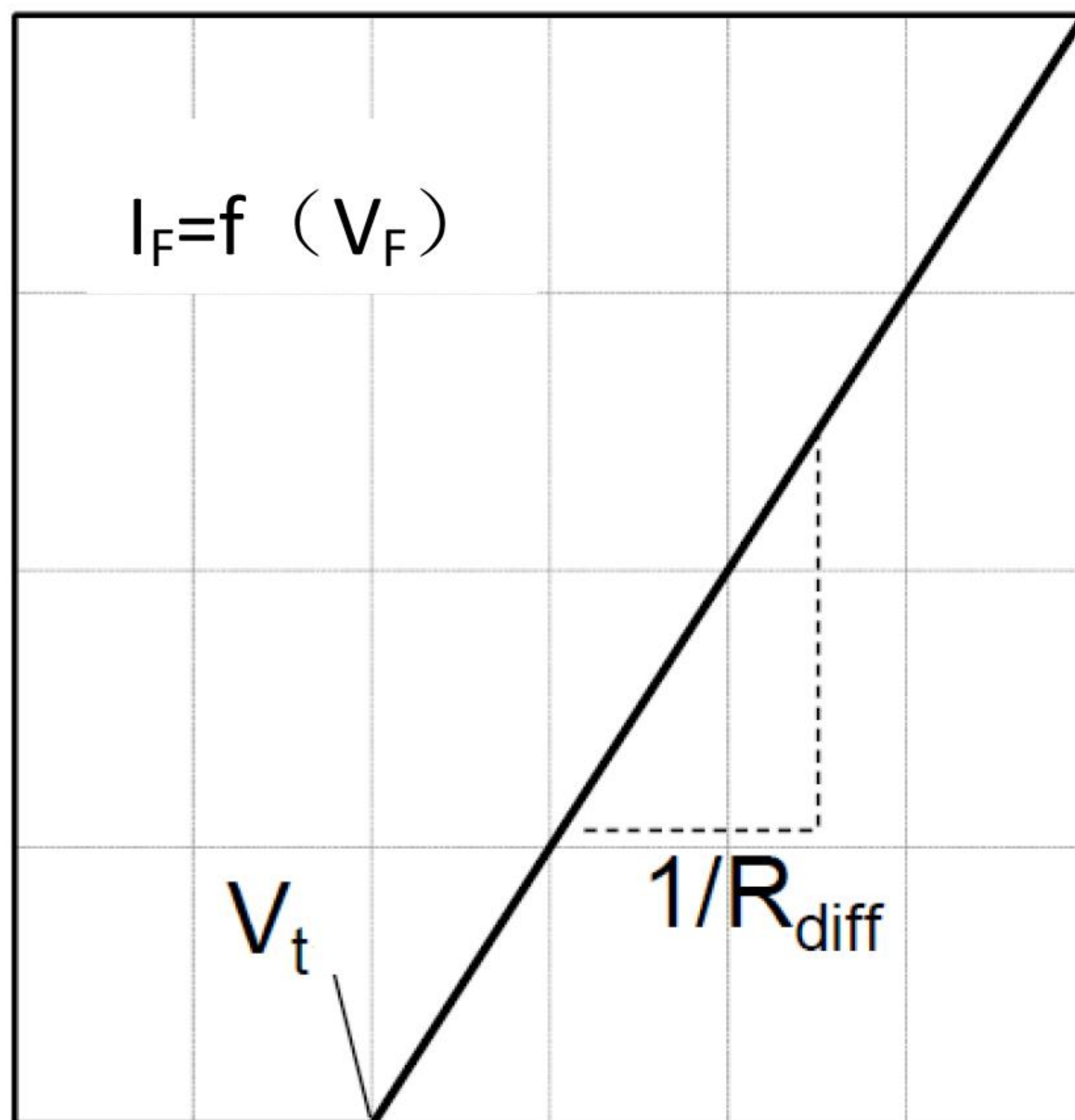
Package TO-247-2



Symbol	Min. (mm)	Typ. (mm)	Max. (mm)
A	14.18	15.75	17.33
B	18.45	20.5	22.55
C	4.50	5.00	5.50
D	3.15	3.50	3.85
E	1.08	1.20	1.32
F	18.27	20.30	22.33

Simplified Diode Model

Equivalent IV Curve for Model



Mathematical Equation

$$V_F = V_t + I_F \times R_{diff}$$

$$V_t = -0.00129 \times T_j + 1.02185 \text{ [V]}$$

$$R_{diff} = 3.99 \times 10^{-7} \times T_j^2 + 2.96 \times 10^{-5} \times T_j + 0.011 \text{ [\Omega]}$$

Note:

T_j = Diode Junction Temperature In Degrees Celsius,
valid from 25°C to 175°C

I_F = Forward Current

Less than 100A